

**isc Silicon PNP Power Transistor**
**2SA1225**
**DESCRIPTION**

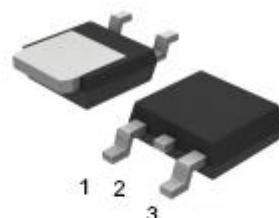
- High transition frequency
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation
- Complementary to 2SC2983

**APPLICATIONS**

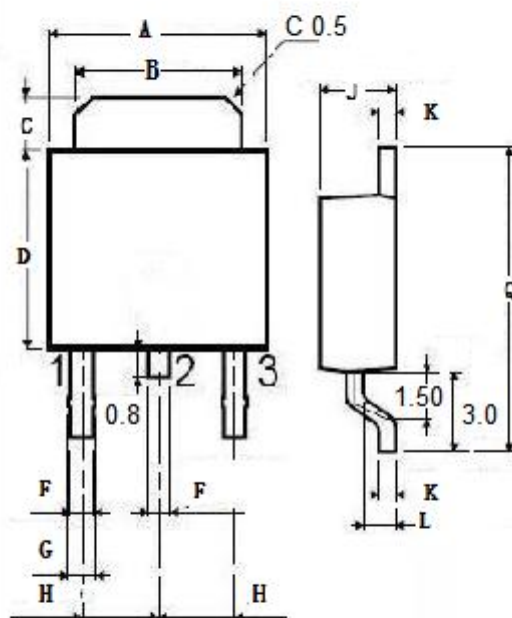
- Power amplifier applications
- Driver stage amplifier applications

**ABSOLUTE MAXIMUM RATINGS(T<sub>a</sub>=25°C)**

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>CB0</sub>	Collector-Base Voltage	-160	V
V <sub>CEO</sub>	Collector-Emitter Voltage	-160	V
V <sub>EBO</sub>	Emitter-Base Voltage	-5	V
I <sub>C</sub>	Collector Current-Continuous	-1.5	A
P <sub>C</sub>	Total Power Dissipation @ T <sub>C</sub> =25°C	1	W
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature Range	-55~150	°C

**DPAK**


T0-252 package

 PIN: 1. BASE  
2. COLLECTOR  
3. EMITTER


DIM	mm	
	MIN	MAX
A	6.40	6.60
B	5.20	5.40
C	1.15	1.35
D	5.70	6.10
F	0.65	
G	0.75	
H	2.10	2.50
J	2.10	2.40
K	0.40	0.60
L	0.90	1.10
Q	9.90	10.1

**isc Silicon PNP Power Transistor****2SA1225****ELECTRICAL CHARACTERISTICS**T<sub>c</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> =-1mA, I <sub>C</sub> =0	-5			V
V <sub>(BR)CEO</sub> <sup>NOTE</sup>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> =-10mA, I <sub>B</sub> =0	-160			V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> =-1mA, I <sub>E</sub> =0	-160			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -0.5A; I <sub>B</sub> = -50mA			-1.5	V
V <sub>BE(on)</sub>	Base-Emitter Voltage	V <sub>CE</sub> =-5V, I <sub>C</sub> =-0.5A			-1.0	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = -160V; I <sub>E</sub> = 0			-0.1	μ A
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = -5V; I <sub>C</sub> =0			-0.1	μ A
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = -0.1A; V <sub>CE</sub> = -5V	70		240	
f <sub>T</sub>	Transition frequency	V <sub>CE</sub> =-10V, I <sub>C</sub> =-100mA		100		MHz
C <sub>ob</sub>	Collector output capacitance	V <sub>CB</sub> =-10V, I <sub>E</sub> =0, f=1MHz		30		pF

NOTE:Pulse test

◆ **h<sub>FE</sub> Classifications**

O	Y
70-140	120-240

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